L Number	Hits	Search Text	DB	Time stamp
	1287	438/197	USPAT	2004/05/28 13:22
2	192	438/249	USPAT	2004/05/28 13:22
3	212	438/251	USPAT	2004/05/28 13:22
4	2122	438/257	USPAT	2004/05/28 13:22
5 6	483	438/267	USPAT	2004/05/28 13:22
6	842	438/289	USPAT	2004/05/28 13:22
7	1866	438/303	USPAT	2004/05/28 13:23
8	2399	438/305	USPAT	2004/05/28 13:23
9	887	438/306	USPAT	2004/05/28 13:23
10	719	438/307	USPAT	2004/05/28 13:23
11	332	438/311	USPAT	2004/05/28 13:23
12	1002	438/680	USPAT	2004/05/28 13:23
13	487	438/681	USPAT	2004/05/28 13:23
14	346	438/663	USPAT	2004/05/28 13:24
15	1	("6233094").PN.	USPAT	2004/05/28 13:24
16	i	("6323094").PN.	USPAT	2004/05/28 13:25
17	1	("6221746").PN.		•
I	1	,	USPAT	2004/05/28 13:25
18]	("6214656").PN.	USPAT	2004/05/28 13:27
19	1	("6153520").PN.	USPAT	2004/05/28 13:27
20	1	("6008099").PN.	USPAT	2004/05/28 13:27
21	1	("5920774").PN.	USPAT	2004/05/28 13:28
22	1	("5792699").PN.	USPAT	2004/05/28 13:29
23	1	("5726477").PN.	USPAT	2004/05/28 13:29
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-	1	"5750435".PN. and (MOSFET or tilt or angle or	USPAT	2004/05/26 15:36
		polysilicon or gate or electrode or insulating or oxide or		
		silicon or GaAs or SOI or source or drain or region or LDD		
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